



### Description

The NTMS4816N uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



SOP-8

### General Features

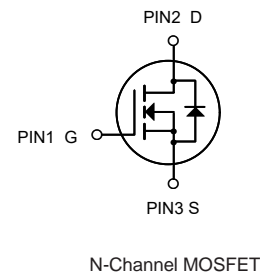
$V_{DS} = 30V$   $I_D = 15A$

$R_{DS(ON)} < 9m\Omega$  @  $V_{GS}=10V$

$R_{DS(ON)} < 14m\Omega$  @  $V_{GS}=4.5V$

### Application

- Battery protection
- Load switch
- Uninterruptible power supply



### Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
NTMS4816N	SOP-8	HXY MOSFET	3000

### Absolute Maximum Ratings ( $T_c=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current-Continuous	15.0	A
$I_D(70^\circ C)$	Drain Current-Continuous( $T_c=70^\circ C$ )	8.2	A
$I_{DM}$	Pulsed Drain Current	42	A
$P_D$	Maximum Power Dissipation	1.5	W
$E_{AS}$	Single pulse avalanche energy (Note 5)	62	mJ
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 To 150	$^\circ C$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 2)	36	$^\circ C/W$



**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	$BV_{DSS}$ Temperature Coefficient	Reference to $25^\circ\text{C}$ , $I_D=1\text{mA}$	---	0.027	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=10A$	---	7.5	9	m $\Omega$
		$V_{GS}=4.5V, I_D=8A$	---	11	14	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.5	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.8	---	$\text{mV}/^\circ\text{C}$
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=24V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	$\mu\text{A}$
		$V_{DS}=24V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA
$g_{fs}$	Forward Transconductance	$V_{DS}=5V, I_D=10A$	---	5.8	---	S
$R_g$	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	2.2	3.8	$\Omega$
$Q_g$	Total Gate Charge (4.5V)	$V_{DS}=15V, V_{GS}=4.5V, I_D=10A$	---	12.6	17.6	nC
$Q_{gs}$	Gate-Source Charge		---	4.2	5.9	
$Q_{gd}$	Gate-Drain Charge		---	5.1	7.1	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V, V_{GS}=10V, R_G=3.3\Omega, I_D=10A$	---	6.2	12.4	ns
$T_r$	Rise Time		---	59	106	
$T_{d(off)}$	Turn-Off Delay Time		---	27.6	55	
$T_f$	Fall Time		---	8.4	16.8	
$C_{iss}$	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$	---	1317	1845	pF
$C_{oss}$	Output Capacitance		---	163	228.2	
$C_{rss}$	Reverse Transfer Capacitance		---	131	183.4	
$I_S$	Continuous Source Current <sup>1,5</sup>	$V_G=V_D=0V$ , Force Current	---	---	10.3	A
$I_{SM}$	Pulsed Source Current <sup>2,5</sup>		---	---	42	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1.2	V
$t_{rr}$	Reverse Recovery Time	$I_F=10A, dI/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	12.5	---	nS
$Q_{rr}$	Reverse Recovery Charge		---	5	---	nC

Note :

1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
2. The data tested by pulsed, pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$
3. The EAS data shows Max. rating. The test condition is  $V_{DD}=25V, V_{GS}=10V, L=0.1\text{mH}, I_{AS}=35A$
4. The power dissipation is limited by  $150^\circ\text{C}$  junction temperature
5. The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications, should be limited by total power dissipation.



### Typical Characteristics

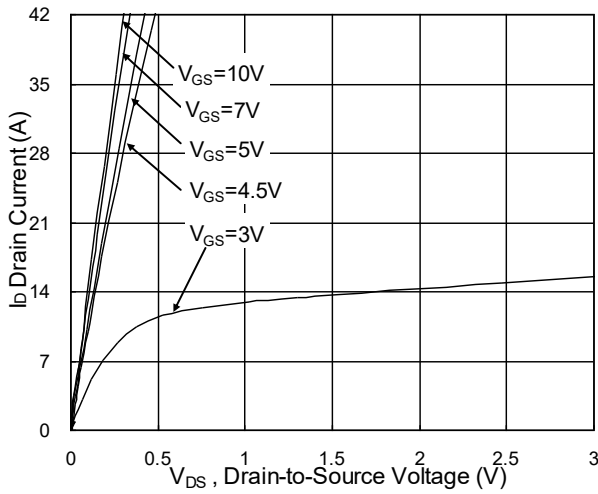


Fig.1 Typical Output Characteristics

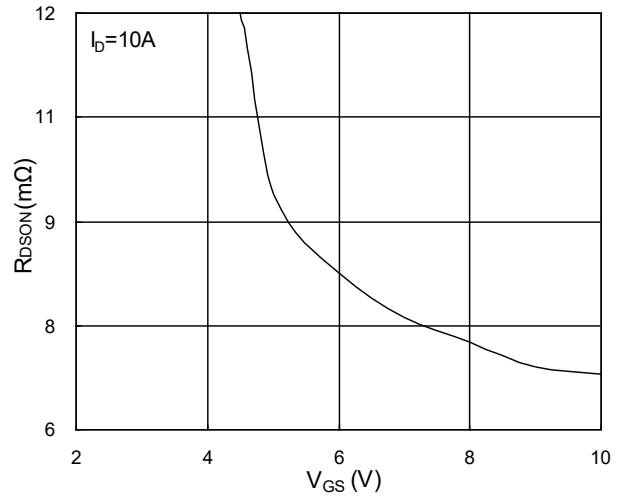


Fig.2 On-Resistance vs. Gate-Source

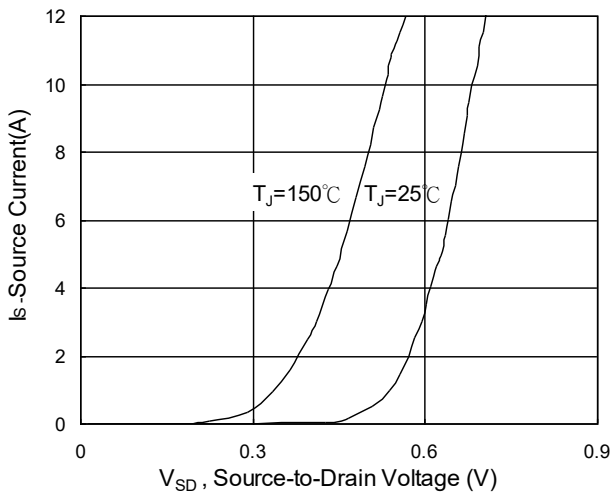


Fig.3 Forward Characteristics of reverse

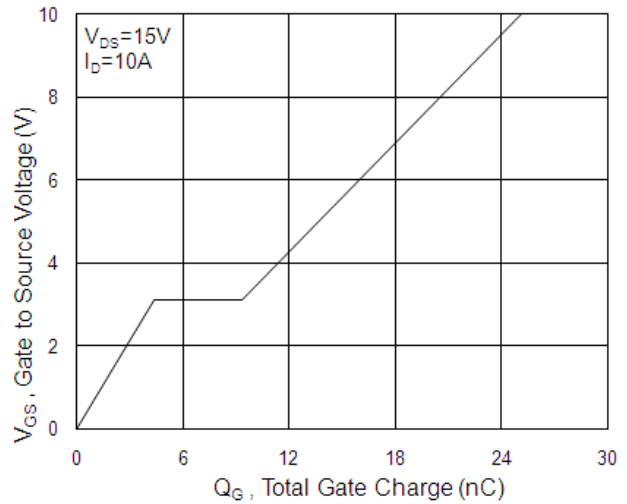


Fig.4 Gate-Charge Characteristics

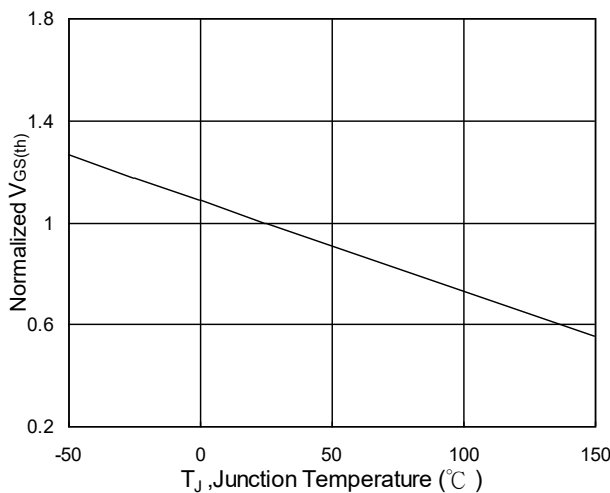


Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$

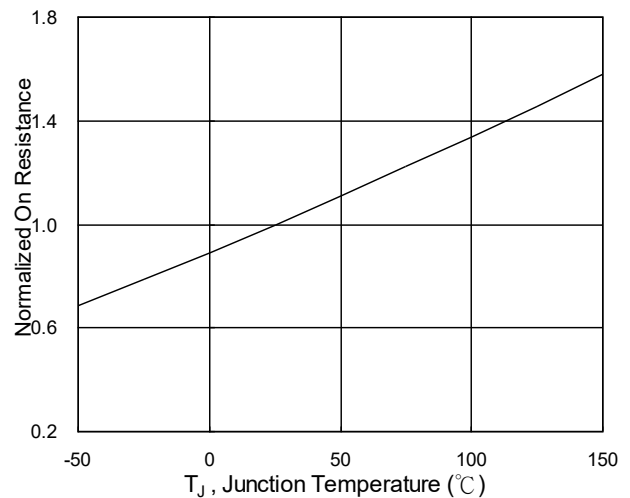


Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$

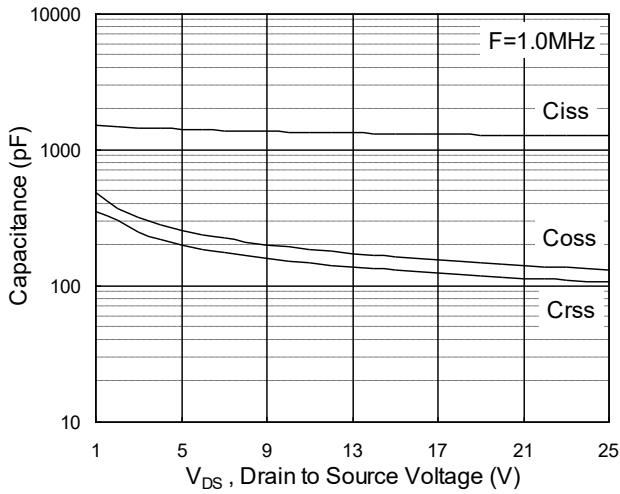


Fig.7 Capacitance

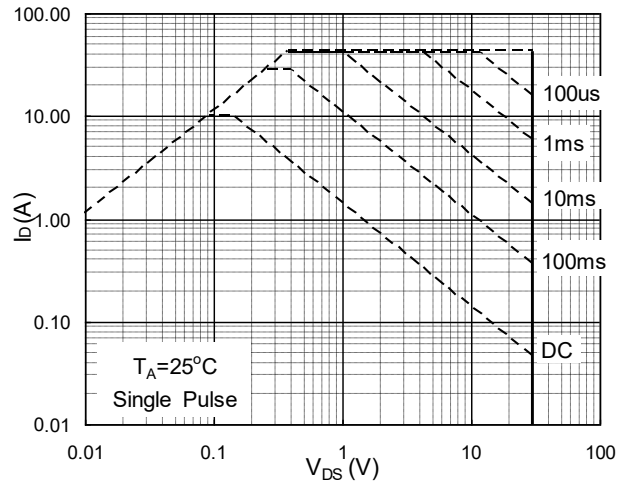


Fig.8 Safe Operating Area

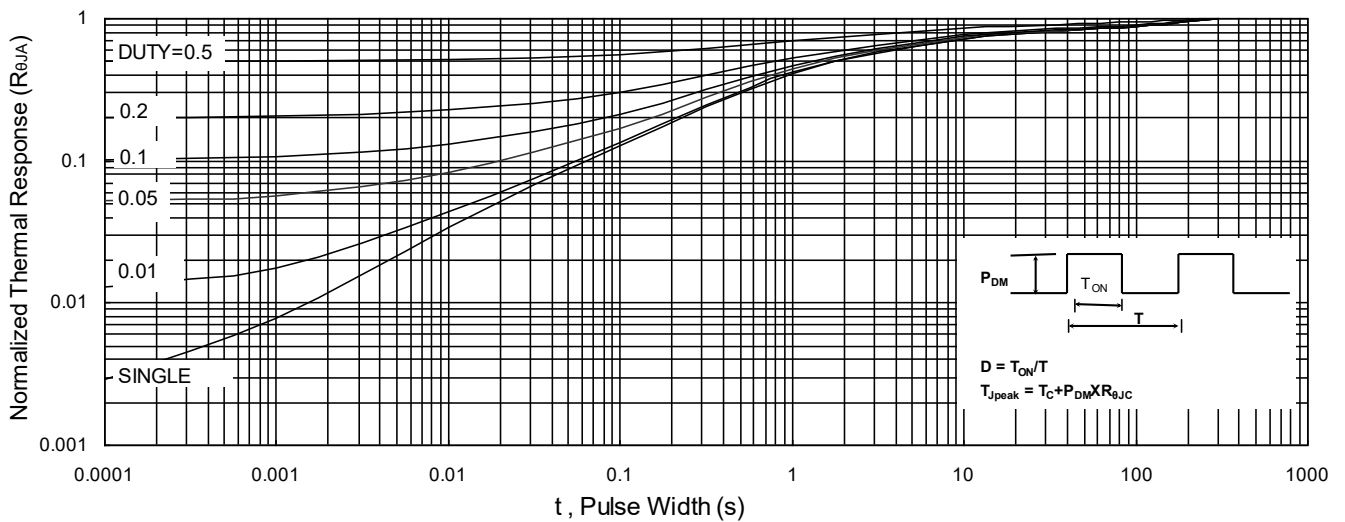


Fig.9 Normalized Maximum Transient Thermal Impedance



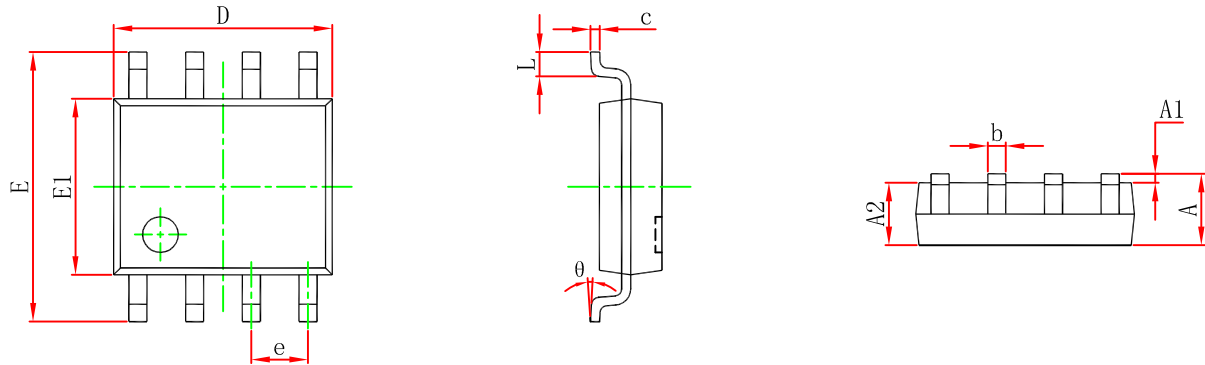
Fig.10 Switching Time Waveform



Fig.11 Unclamped Inductive Switching Waveform



### SOP-8 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



- Note:
1. Controlling dimension: in millimeters.
  2. General tolerance:  $\pm 0.05\text{mm}$ .
  3. The pad layout is for reference purposes only.



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